

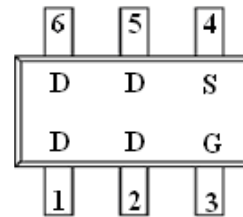
➤ General Description

This PAN0080H N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

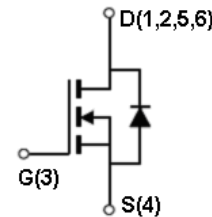
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- SOT-363 package design

➤ SOT-363



➤ Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Load/Power Switching Smart Phones, Pagers
- PA Switch
- Level Switch



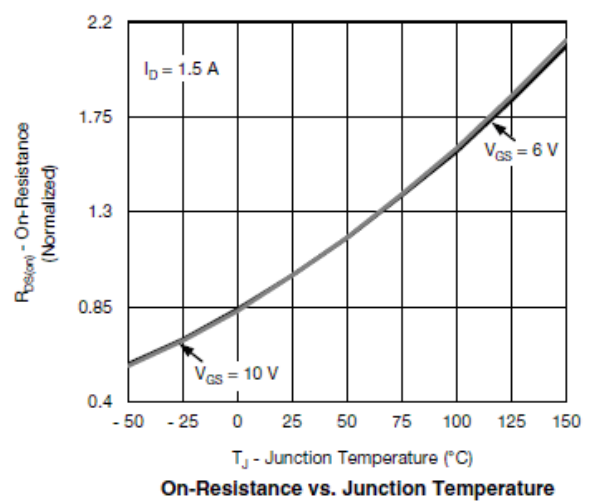
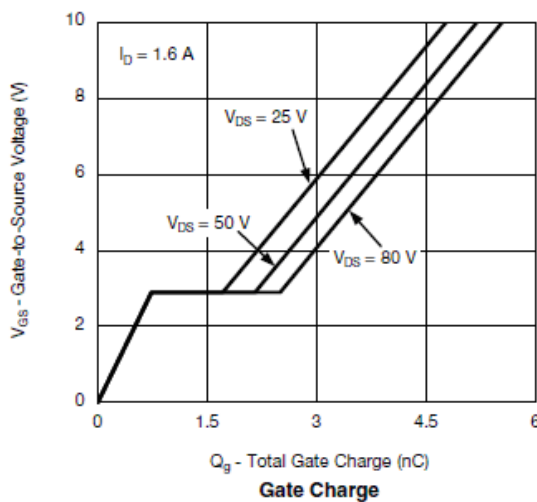
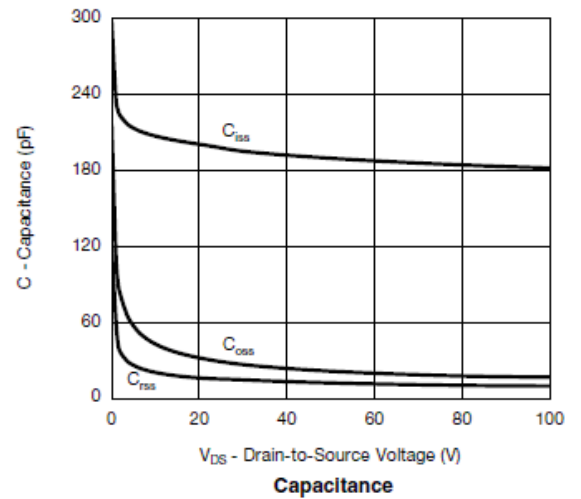
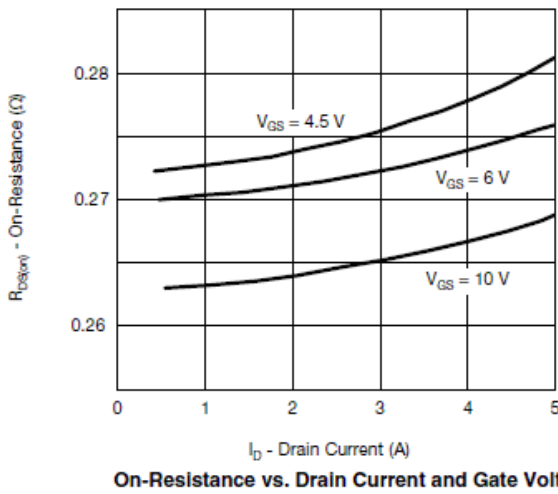
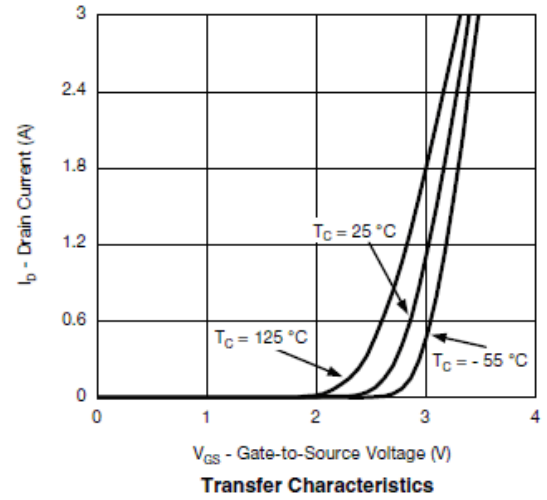
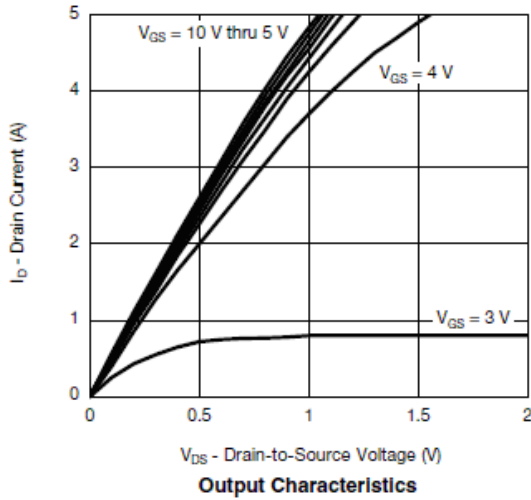
➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate -Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current($T_J=150^\circ C$)	I_D	$T_A=25^\circ C$	2.3
		$T_A=70^\circ C$	1.8
Pulsed Drain Current	I_{DM}	7	A
Continuous Source Current(Diode Conduction)	I_S	1.3	A
Power Dissipation	P_D	$T_A=25^\circ C$	1.5
		$T_A=70^\circ C$	1.0
Operating Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ C/W$

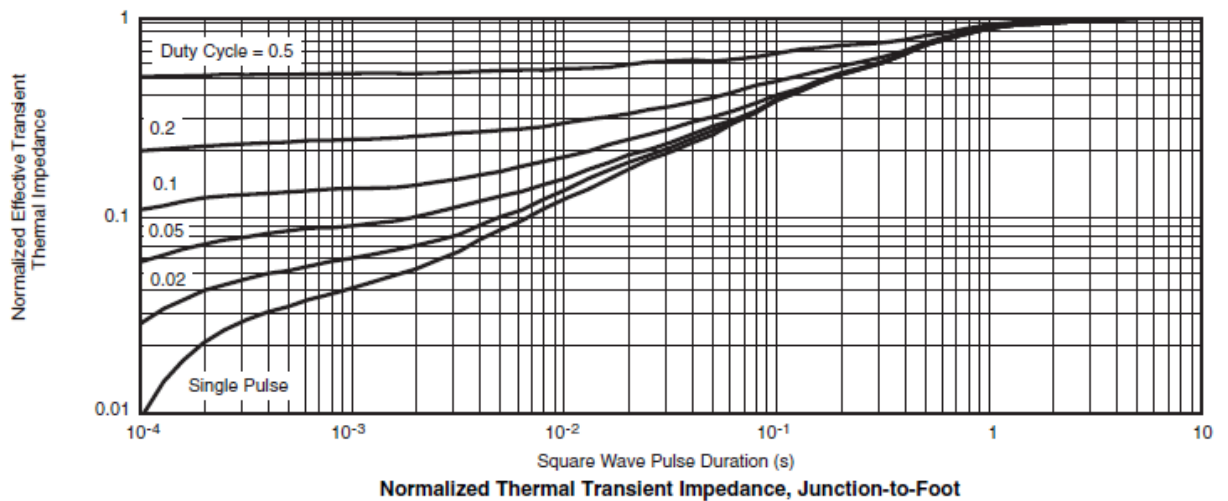
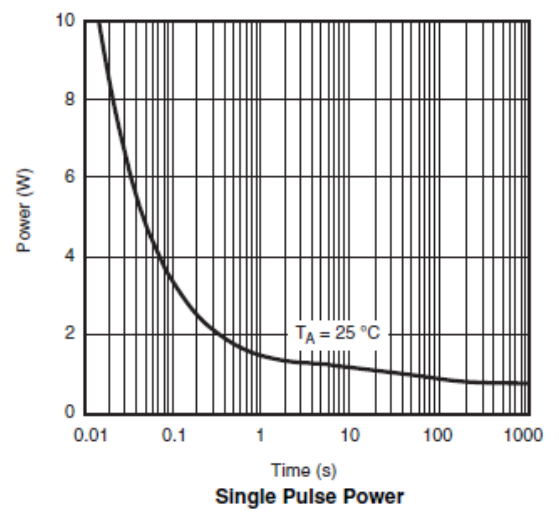
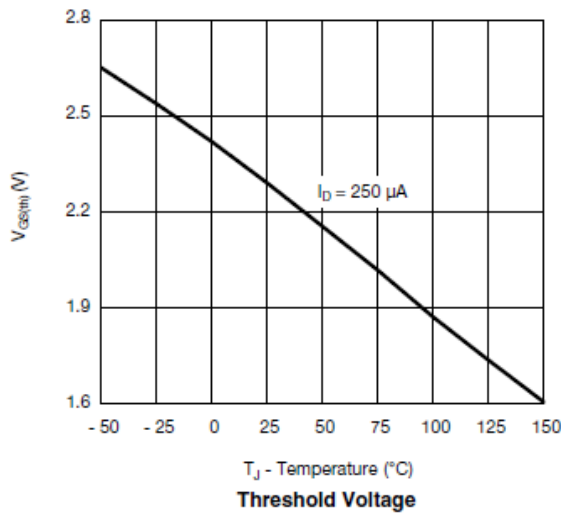
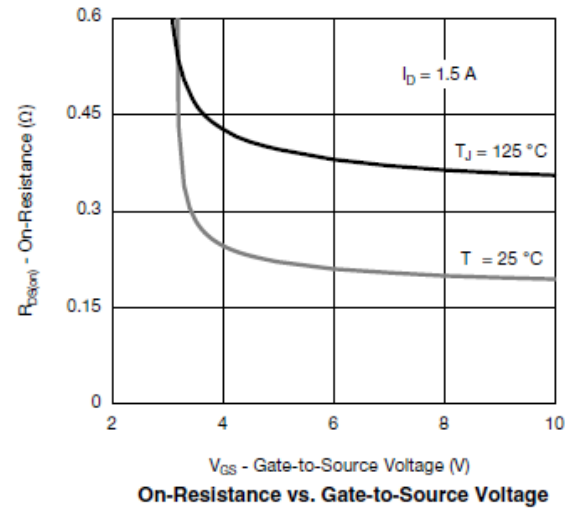
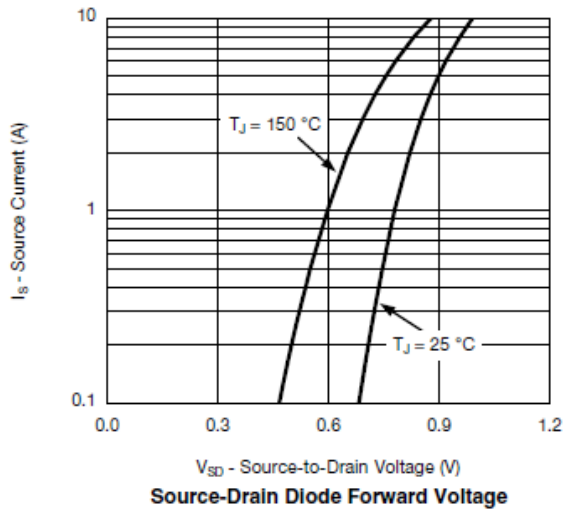
➤ **Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)**

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.0	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			1	uA
		$V_{DS}=80V, V_{GS}=0V$ $T_J=85^\circ C$			10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	5			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2.3A$		265	285	m Ω
		$V_{GS}=4.5V, I_D=1.8A$		275	295	
Forward Transconductance	g_{FS}	$V_{DS}=20V, I_D=1.5A$		2		S
Diode Forward Voltage	V_{SD}	$I_S=1.3A, V_{GS}=0V$		0.85	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=50V, V_{GS}=4.5V$ $I_D \approx 1.6A$		2.8	5.8	nC
Gate-Source Charge	Q_{gs}			0.75		
Gate-Drain Charge	Q_{gd}			1.4		
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V$ $f=1MHz$		200		pF
Output Capacitance	C_{oss}			22		
Reverse Transfer Capacitance	C_{rss}			13		
Turn-On Time	$t_{d(on)}$	$V_{DD}=50V, R_L=39\Omega$ $I_D \approx 1.3A, V_{GEN}=4.5V$ $R_G=1\Omega$		25	50	ns
	t_r			20	50	
Turn-Off Time	$t_{d(off)}$			15	30	
	t_f			10	25	

➤ Typical Characteristics



N-Ch 100V Fast Switching MOSFET
 $V_{DS}=100V, I_D=2.3A, R_{DS(ON)}=285m\Omega$



➤ Recommand IR Reflow Soldering Thermal Profile

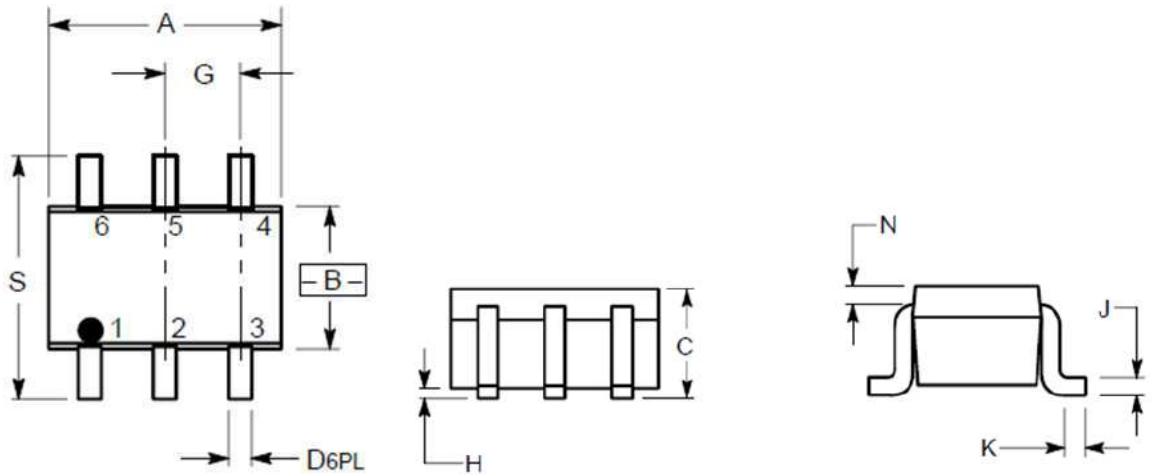


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN0080H	SOT-363 Reel	3000 pcs

➤ Package Information (SOT-363)



\oplus	0.2 (0.008) $\text{\textcircled{M}}$	B $\text{\textcircled{M}}$
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DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

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